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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Li et al.

I hereby certify that this paper is being facsimile transmitted to the U.S. Patent and Trademark Office on this date.

Serial No.: 09/662,682

Nov. 4, 2002 Chris B. R.
Date profax.wcm Registration No. 43,574

Filed: September 15, 2000

Appl. April 11, 2000 Attorney for Applicant

For: METAL-ASSISTED CHEMICAL
ETCH POROUS SILICON
FORMATION METHOD

Art Unit: 1765

Examiner: Vinh, Lan

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AMENDMENT CAssistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Office Action mailed August 2, 2002, please amend the application as follows:

In the Claims:

Please amend claims 1, 11, and 21 to read as follows:

1. (Amended) A method for producing porous silicon, the method comprising steps of:

B1
 depositing a thin discontinuous layer of metal on a Si surface;
 forming the porous silicon by etching the Si surface in a HF and oxidant solution, said etching being conducted without external electrical bias.